

# SILICON MIXER DIODE

**DESCRIPTION:**

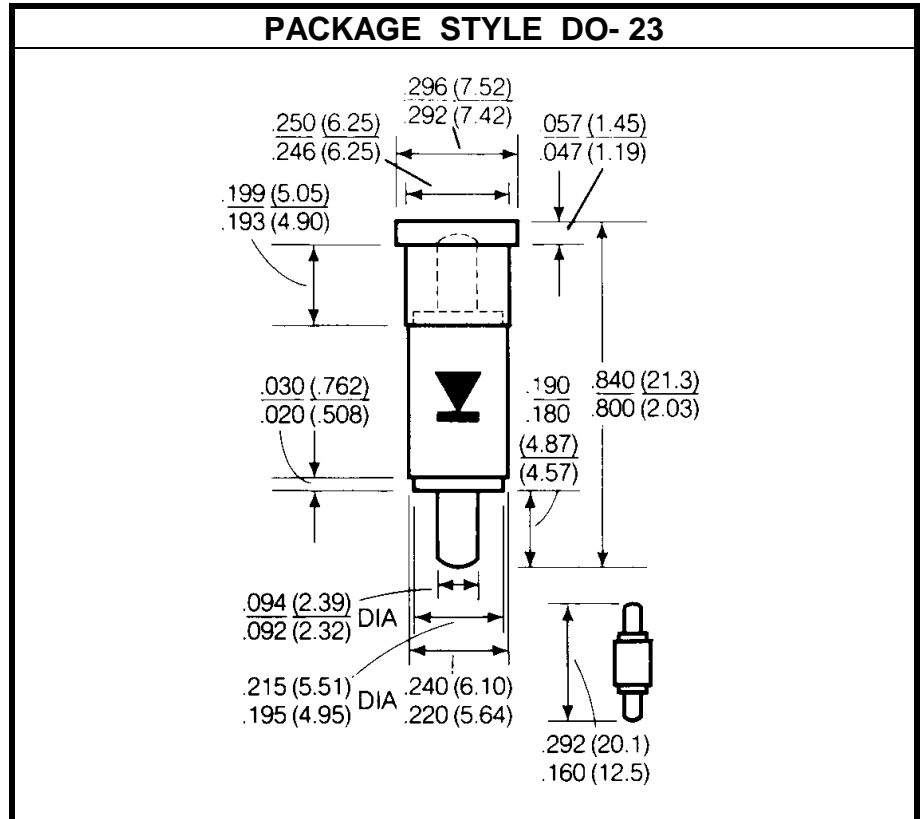
The **ASI 1N23WE** is a Silicon Mixer Diode Designed for Applications Operating From 8.0 to 12.4 GHz.

**FEATURES:**

- High burnout resistance
- Low noise figure
- Hermetically sealed package

**MAXIMUM RATINGS**

<b>I<sub>F</sub></b>	20 mA
<b>V<sub>R</sub></b>	1.0 V
<b>P<sub>DISS</sub></b>	5.0 (ERGS) @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +150 °C
<b>T<sub>STG</sub></b>	-55 °C to +150 °C


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
<b>N<sub>F</sub></b>	F = 9375 MHz R <sub>L</sub> = 100 Ω P <sub>io</sub> = 1.0 mW I <sub>F</sub> = 30 MHz N <sub>Fif</sub> = 1.5 dB			7.5	<b>dB</b>
<b>V<sub>SWR</sub></b>				1.3	
<b>Z<sub>IF</sub></b>	R <sub>L</sub> = 22 Ω f = 1000 Hz	335		465	<b>Ω</b>
<b>frange</b>		8.0		12.4	<b>GHz</b>